

SURFACE MOUNT SILICON SCHOTTKY DIODES



Central
Semiconductor Corp.

www.centralsemi.com

## DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMSSH-3 Series types are Silicon Schottky Diodes, epoxy molded in a SUPERmini<sup>™</sup> surface mount package, designed for fast switching applications requiring a low forward voltage drop.

MAXIMUM RATINGS: (T <sub>A</sub> =25°C)	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	30	V
Continuous Forward Current	١ <sub>F</sub>	100	mA
Peak Repetitive Forward Current	IFRM	200	mA
Peak Forward Surge Current, tp=10ms	IFSM	750	mA
Power Dissipation	PD	275	mW
Operating and Storage Junction Temperature	Т <sub>Ј</sub> , Т <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	ΘJΑ	455	°C/W

## ELECTRICAL CHARACTERISTICS PER DIODE: (T<sub>A</sub>=25°C unless otherwise noted)

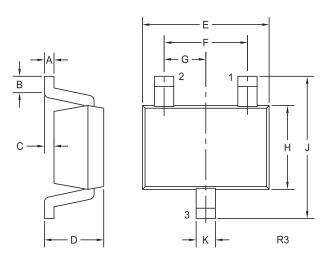
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
I <sub>R</sub>	V <sub>R</sub> =25V		90	500	nA	
I <sub>R</sub>	V <sub>R</sub> =25V, T <sub>A</sub> =100°C		25	100	μA	
BVR	I <sub>R</sub> =100μΑ	30			V	
VF	I <sub>F</sub> =2.0mA		0.29	0.33	V	
VF	I <sub>F</sub> =15mA		0.40	0.45	V	
VF	I <sub>F</sub> =100mA		0.74	1.00	V	
С <sub>Т</sub>	V <sub>R</sub> =1.0V, f=1.0MHz		7.0		pF	
t <sub>rr</sub>	$I_F = I_R = 10$ mA, $I_{rr} = 1.0$ mA, $R_L = 100\Omega$			5.0	ns	

R3 (9-February 2010)



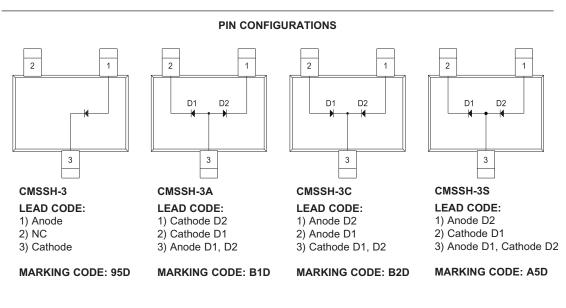
CMSSH-3 CMSSH-3A CMSSH-3C CMSSH-3S

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DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
А	0.002	0.008	0.05	0.20			
В	0.004	-	0.10	-			
С	-	0.004	-	0.10			
D	0.031	0.043	0.80	1.10			
E	0.071	0.087	1.80	2.20			
F	0.051		1.30				
G	0.026		0.65				
Н	0.045	0.053	1.15	1.35			
J	0.079	0.087	2.00	2.20			
K	0.008	0.016	0.20	0.40			
SOT-323 (REV/· R3)							

SOT-323 (REV: R3)



SOT-323 CASE - MECHANICAL OUTLINE

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